

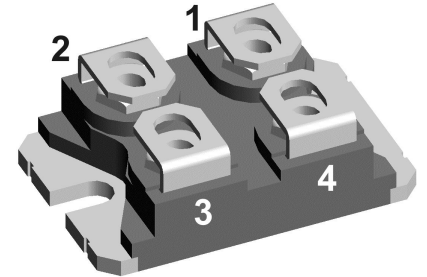
# Standard Rectifier

<b>3~ Rectifier</b>	
$V_{RRM}$	= 1600 V
$I_{DAV}$	= 240 A
$I_{FSM}$	= 1300 A

Half 3~ Bridge, Common Cathode

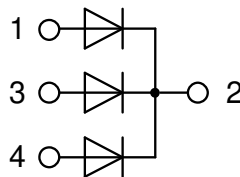
Part number

**DMA240YC1600NA**



Backside: isolated

E72873



### Features / Advantages:

- Planar passivated chips
- Very low leakage current
- Very low forward voltage drop
- Improved thermal behaviour

### Applications:

- Diode for main rectification
- For single and three phase bridge configurations

### Package: SOT-227B (minibloc)

- Isolation Voltage: 3000 V~
- Industry standard outline
- RoHS compliant
- Epoxy meets UL 94V-0
- Base plate: Copper internally DCB isolated
- Advanced power cycling

### Terms and Conditions of Usage

The data contained in this product data sheet is exclusively intended for technically trained staff. The user will have to evaluate the suitability of the product for the intended application and the completeness of the product data with respect to his application. The specifications of our components may not be considered as an assurance of component characteristics. The information in the valid application- and assembly notes must be considered. Should you require product information in excess of the data given in this product data sheet or which concerns the specific application of your product, please contact your local sales office.

Due to technical requirements our product may contain dangerous substances. For information on the types in question please contact your local sales office.

Should you intend to use the product in aviation, in health or life endangering or life support applications, please notify. For any such application we urgently recommend

- to perform joint risk and quality assessments;

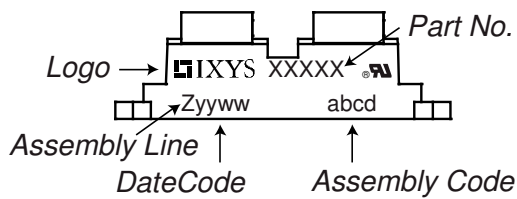
- the conclusion of quality agreements;

- to establish joint measures of an ongoing product survey, and that we may make delivery dependent on the realization of any such measures.

Rectifier				Ratings			
Symbol	Definition	Conditions		min.	typ.	max.	Unit
$V_{RSM}$	max. non-repetitive reverse blocking voltage			$T_{VJ} = 25^{\circ}\text{C}$		1700	V
$V_{RRM}$	max. repetitive reverse blocking voltage			$T_{VJ} = 25^{\circ}\text{C}$		1600	V
$I_R$	reverse current	$V_R = 1600\text{ V}$		$T_{VJ} = 25^{\circ}\text{C}$		50	$\mu\text{A}$
		$V_R = 1600\text{ V}$		$T_{VJ} = 150^{\circ}\text{C}$		1.5	mA
$V_F$	forward voltage drop	$I_F = 80\text{ A}$		$T_{VJ} = 25^{\circ}\text{C}$		1.23	V
		$I_F = 240\text{ A}$				1.72	V
		$I_F = 80\text{ A}$		$T_{VJ} = 125^{\circ}\text{C}$		1.19	V
		$I_F = 240\text{ A}$				1.80	V
$I_{DAV}$	bridge output current	$T_C = 100^{\circ}\text{C}$		$T_{VJ} = 150^{\circ}\text{C}$		240	A
		rectangular	$d = \frac{1}{3}$				
$V_{FO}$	threshold voltage			$T_{VJ} = 150^{\circ}\text{C}$		0.86	V
$r_F$	slope resistance					4	$\text{m}\Omega$
						} for power loss calculation only	
$R_{thJC}$	thermal resistance junction to case					0.35	K/W
$R_{thCH}$	thermal resistance case to heatsink				0.10		K/W
$P_{tot}$	total power dissipation			$T_C = 25^{\circ}\text{C}$		355	W
$I_{FSM}$	max. forward surge current	$t = 10\text{ ms}; (50\text{ Hz}), \text{ sine}$		$T_{VJ} = 45^{\circ}\text{C}$		1.30	kA
		$t = 8,3\text{ ms}; (60\text{ Hz}), \text{ sine}$		$V_R = 0\text{ V}$		1.41	kA
		$t = 10\text{ ms}; (50\text{ Hz}), \text{ sine}$		$T_{VJ} = 150^{\circ}\text{C}$		1.11	kA
		$t = 8,3\text{ ms}; (60\text{ Hz}), \text{ sine}$		$V_R = 0\text{ V}$		1.20	kA
$I^2t$	value for fusing	$t = 10\text{ ms}; (50\text{ Hz}), \text{ sine}$		$T_{VJ} = 45^{\circ}\text{C}$		8.45	$\text{kA}^2\text{s}$
		$t = 8,3\text{ ms}; (60\text{ Hz}), \text{ sine}$		$V_R = 0\text{ V}$		8.21	$\text{kA}^2\text{s}$
		$t = 10\text{ ms}; (50\text{ Hz}), \text{ sine}$		$T_{VJ} = 150^{\circ}\text{C}$		6.11	$\text{kA}^2\text{s}$
		$t = 8,3\text{ ms}; (60\text{ Hz}), \text{ sine}$		$V_R = 0\text{ V}$		5.94	$\text{kA}^2\text{s}$
$C_J$	junction capacitance	$V_R = 400\text{ V}; f = 1\text{ MHz}$		$T_{VJ} = 25^{\circ}\text{C}$		48	pF

Package SOT-227B (minibloc)		Ratings				
Symbol	Definition	Conditions	min.	typ.	max.	Unit
$I_{RMS}$	RMS current	per terminal			150	A
$T_{VJ}$	virtual junction temperature		-40		150	°C
$T_{op}$	operation temperature		-40		125	°C
$T_{stg}$	storage temperature		-40		150	°C
<b>Weight</b>				30		g
$M_D$	mounting torque		1.1		1.5	Nm
$M_T$	terminal torque		1.1		1.5	Nm
$d_{Spp/App}$	creepage distance on surface   striking distance through air	terminal to terminal	10.5	3.2		mm
$d_{Spb/Apb}$		terminal to backside	8.6	6.8		mm
$V_{ISOL}$	isolation voltage	t = 1 second		3000		V
		t = 1 minute	50/60 Hz, RMS; $I_{ISOL} \leq 1$ mA	2500		V

### Product Marking



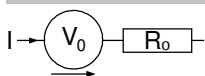
### Part description

- D = Diode
- M = Standard Rectifier
- A = (up to 1800V)
- 240 = Current Rating [A]
- YC = Half 3- Bridge, Common Cathode
- 1600 = Reverse Voltage [V]
- NA = SOT-227B (minibloc)

Ordering	Ordering Number	Marking on Product	Delivery Mode	Quantity	Code No.
Standard	DMA240YC1600NA	DMA240YC1600NA	Tube	10	524738

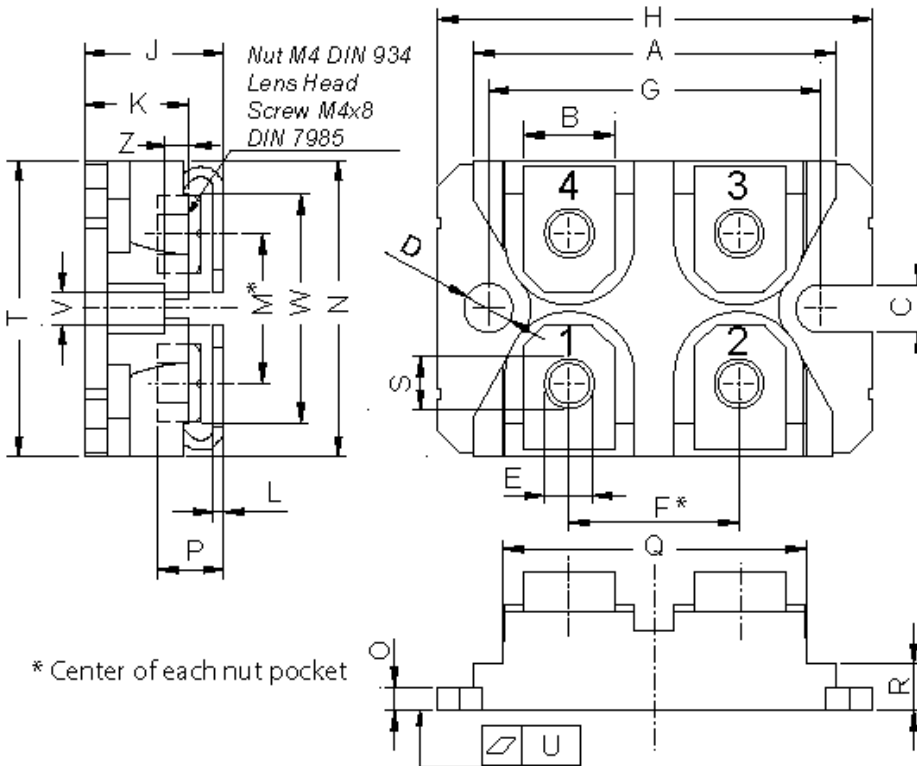
Similar Part	Package	Voltage class
DMA240YA1600NA	SOT-227B (minibloc)	1600

### Equivalent Circuits for Simulation

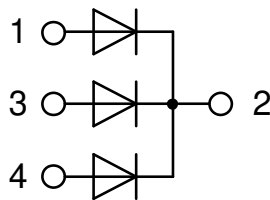
*\* on die level*
 $T_{VJ} = 150\text{ °C}$ 

**Rectifier**

$V_{0\ max}$	threshold voltage	0.86	V
$R_{0\ max}$	slope resistance *	2.1	mΩ

## Outlines SOT-227B (minibloc)



Dim.	Millimeter		Inches	
	min	max	min	max
A	31.50	31.88	1.240	1.255
B	7.80	8.20	0.307	0.323
C	4.09	4.29	0.161	0.169
D	4.09	4.29	0.161	0.169
E	4.09	4.29	0.161	0.169
F	14.91	15.11	0.587	0.595
G	30.12	30.30	1.186	1.193
H	37.80	38.23	1.488	1.505
J	11.68	12.22	0.460	0.481
K	8.92	9.60	0.351	0.378
L	0.74	0.84	0.029	0.033
M	12.50	13.10	0.492	0.516
N	25.15	25.42	0.990	1.001
O	1.95	2.13	0.077	0.084
P	4.95	6.20	0.195	0.244
Q	26.54	26.90	1.045	1.059
R	3.94	4.42	0.155	0.167
S	4.55	4.85	0.179	0.191
T	24.59	25.25	0.968	0.994
U	-0.05	0.10	-0.002	0.004
V	3.20	5.50	0.126	0.217
W	19.81	21.08	0.780	0.830
Z	2.50	2.70	0.098	0.106



## Rectifier

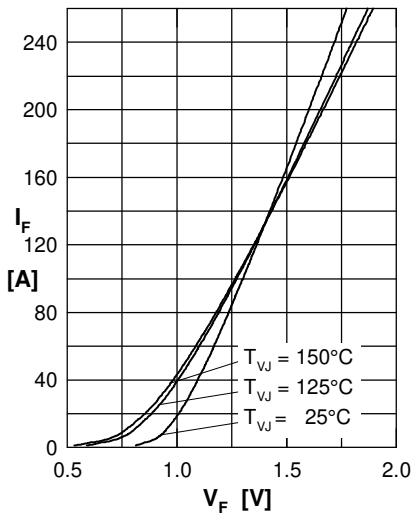


Fig. 1 Forward current versus voltage drop per diode

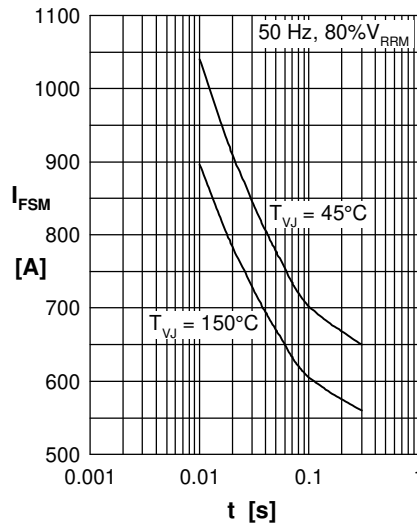


Fig. 2 Surge overload current vs. time per diode

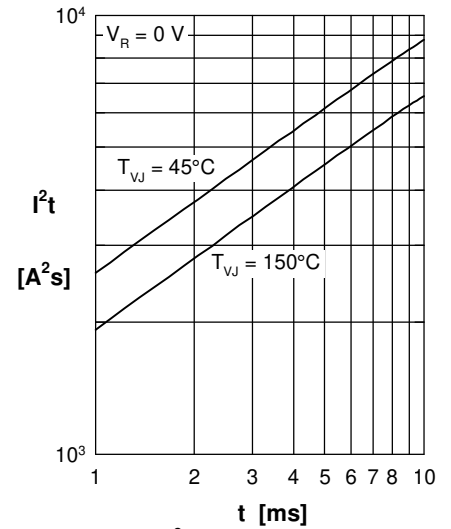


Fig. 3  $I^2t$  versus time per diode

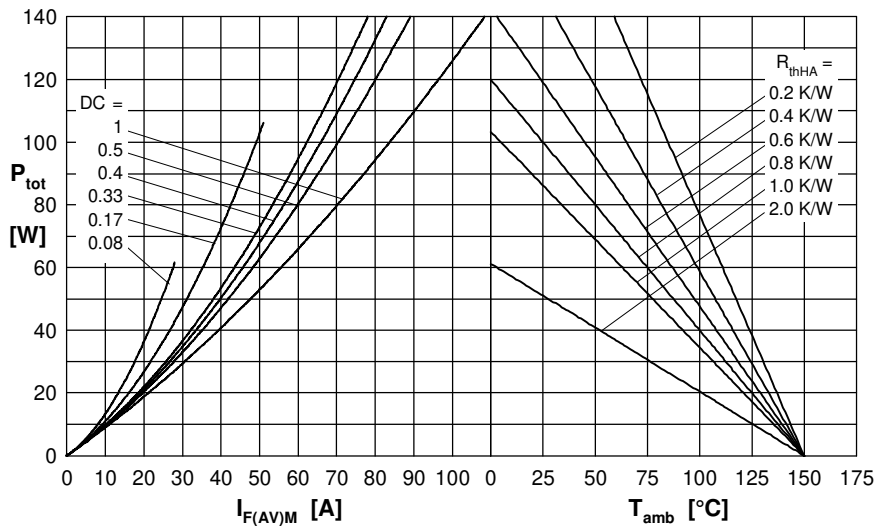


Fig. 4 Power dissipation vs. forward current and ambient temperature per diode

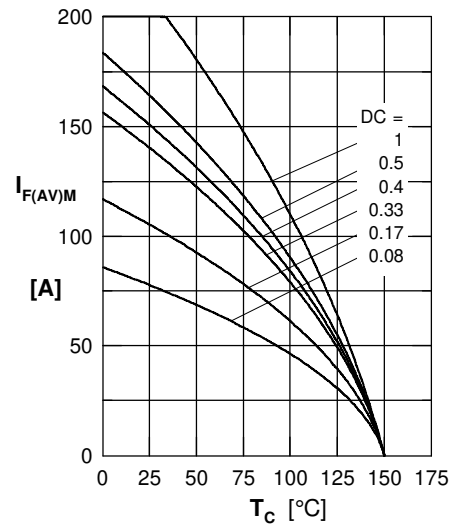


Fig. 5 Max. forward current vs. case temperature per diode

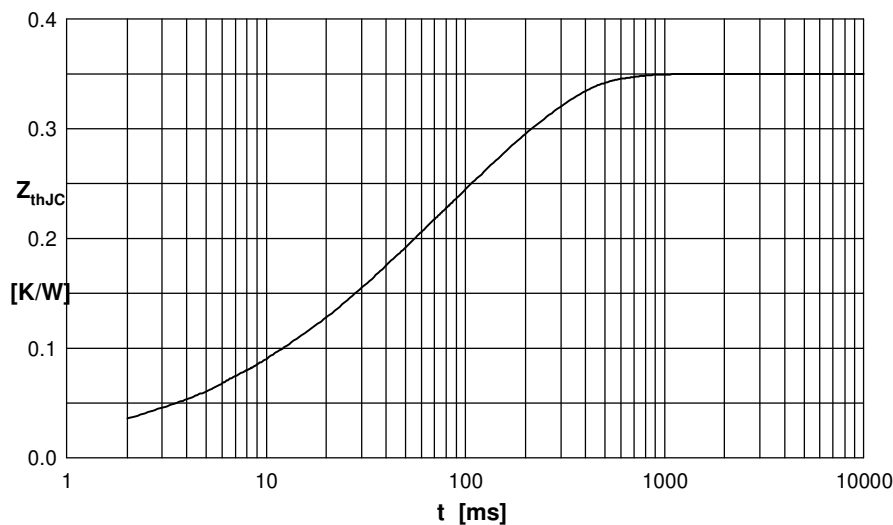


Fig. 6 Transient thermal impedance junction to case vs. time per diode

Constants for  $Z_{thJC}$  calculation:

i	$R_{thi}$ (K/W)	$t_i$ (s)
1	0.0200	0.01000
2	0.0120	0.00001
3	0.0280	0.00400
4	0.1000	0.03000
5	0.1900	0.16000